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# 2SC4988

Silicon NPN Epitaxial

# HITACHI

ADE-208-004  
1st. Edition

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## Application

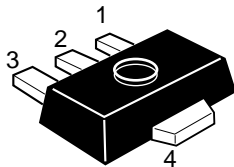
VHF / UHF wide band amplifier

## Features

- High gain bandwidth product  
 $f_T = 8.5 \text{ GHz Typ}$
- High gain, low noise figure  
 $PG = 10.5 \text{ dB Typ}$ ,  $NF = 1.3 \text{ dB Typ}$  at  $f = 900 \text{ MHz}$

## Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)

**Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	15	V
Collector to emitter voltage	$V_{CEO}$	9	V
Emitter to base voltage	$V_{EBO}$	1.5	V
Collector current	$I_C$	100	mA
Collector power dissipation	$P_C$	800*1	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. This value is allowed when using the alumina ceramics board (12.5 x 20 x 0.7 mm)

**Electrical Characteristics** (Ta = 25°C)

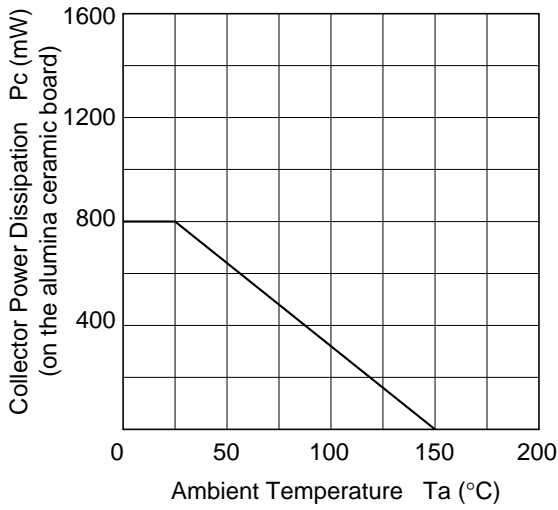
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	$I_{CBO}$	—	—	1	$\mu A$	$V_{CB} = 12 V, I_E = 0$
	$I_{CEO}$	—	—	1	mA	$V_{CE} = 9 V, R_{BE} = \infty$
Emitter cutoff current	$I_{EBO}$	—	—	10	$\mu A$	$V_{EB} = 1.5 V, I_C = 0$
DC current transfer ratio	$h_{FE}$	50	120	250		$V_{CE} = 5 V, I_C = 20 mA$
Collector output capacitance	Cob	—	1.1	1.6	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$
Gain bandwidth product	$f_T$	5.5	8.5	—	GHz	$V_{CE} = 5 V, I_C = 20 mA$
Power gain	PG	7.5	10.5	—	dB	$V_{CE} = 5 V, I_C = 20 mA, f = 900 MHz$
Noise figure	NF	—	1.3	2.5	dB	$V_{CE} = 5 V, I_C = 5 mA, f = 900 MHz$

Note: Marking is "FR".

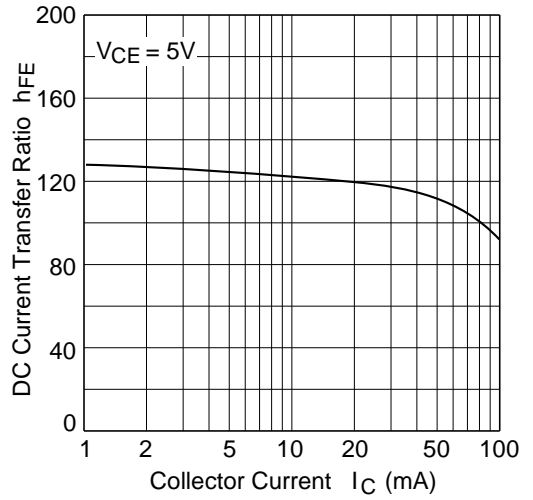
Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

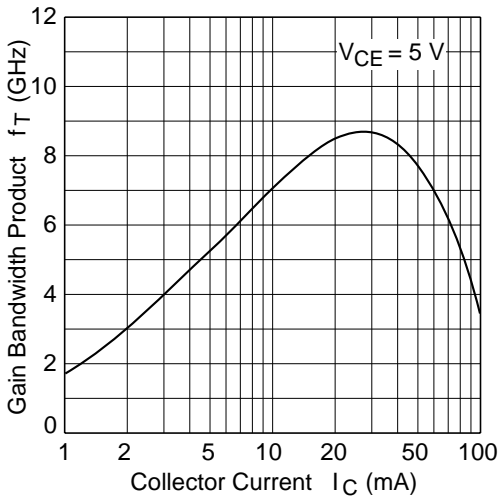
Collector Power Dissipation Curve



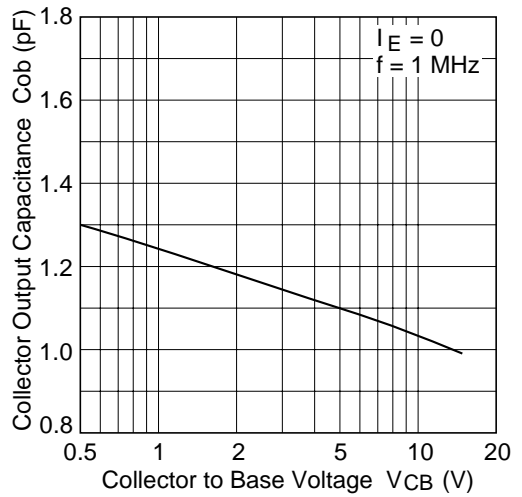
DC Current Transfer Ratio vs. Collector Current



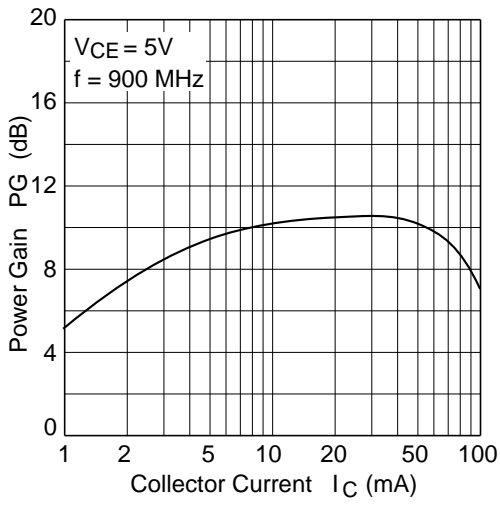
Gain Bandwidth Product vs. Collector Current



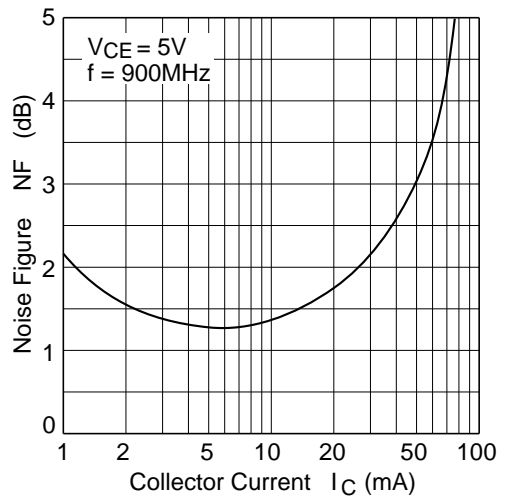
Collector Output Capacitance vs. Collector to Base Voltage



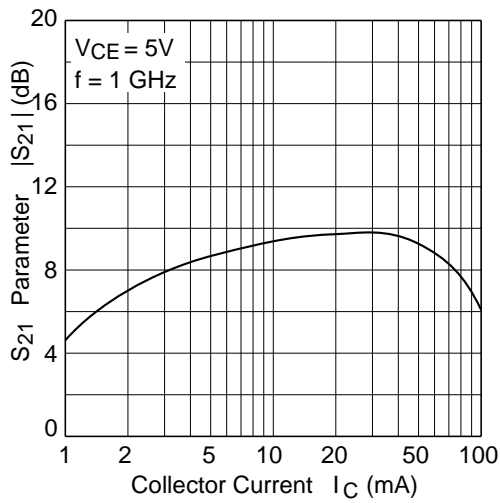
Power Gain vs. Collector Current



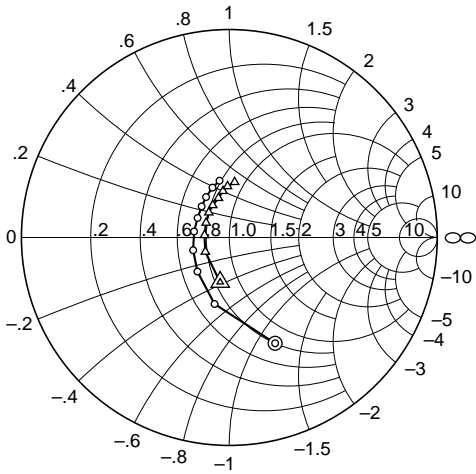
Noise Figure vs. Collector Current



S21 Parameter vs. Collector Current

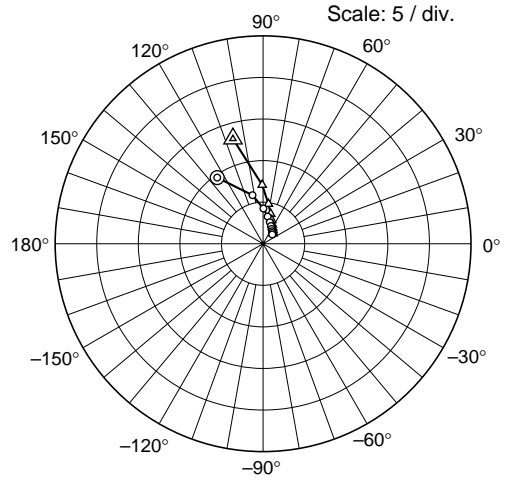


S11 Parameter vs. Frequency



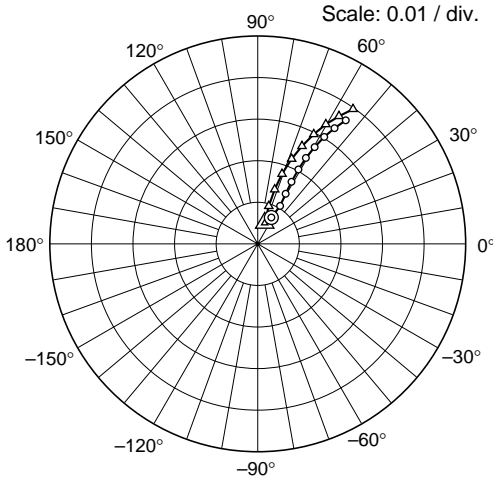
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S21 Parameter vs. Frequency



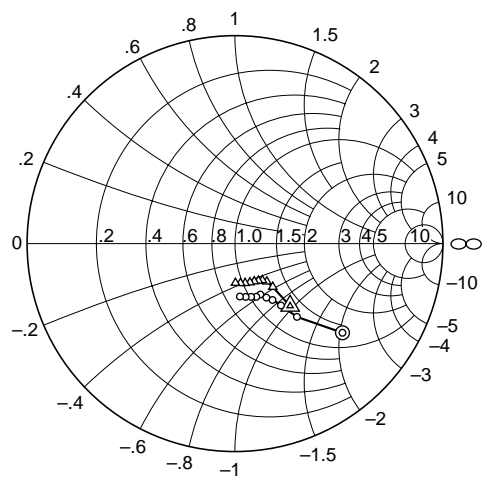
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S12 Parameter vs. Frequency



Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S22 Parameter vs. Frequency



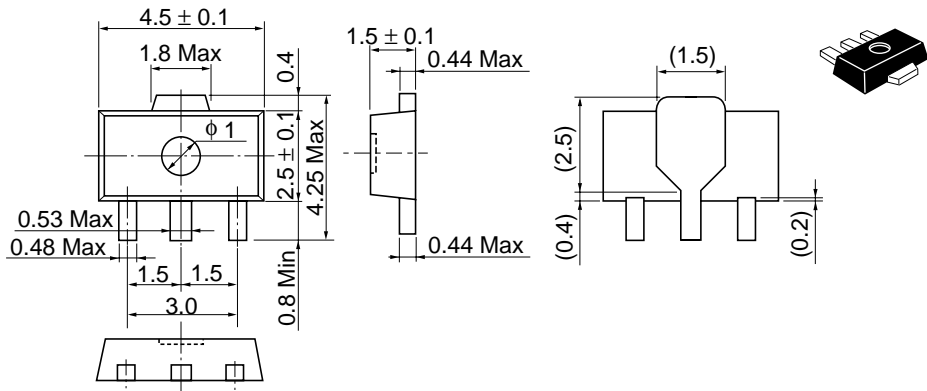
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

**S Parameter** ( $V_{CE} = 5 \text{ V}$ ,  $I_C = 5 \text{ mA}$ ,  $Z_O = 50 \Omega$ )

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.555	-66.6	9.68	124.7	0.0717	62.3	0.672	-39.7
400	0.328	-102.5	5.98	102.2	0.106	59.4	0.462	-49.8
600	0.225	-133.1	4.24	89.3	0.138	60.8	0.371	-53.4
800	0.185	-160.5	3.31	80.3	0.170	61.4	0.326	-56.4
1000	0.172	170.5	2.71	72.4	0.204	61.3	0.301	-59.9
1200	0.179	148.5	2.34	65.8	0.237	60.7	0.285	-63.6
1400	0.200	131.7	2.06	59.9	0.270	59.5	0.276	-68.2
1600	0.224	120.0	1.86	54.4	0.303	58.1	0.268	-73.2
1800	0.253	108.7	1.71	49.6	0.334	56.4	0.262	-78.7
2000	0.277	99.8	1.58	44.9	0.365	54.5	0.256	-84.7

**S Parameter** ( $V_{CE} = 5 \text{ V}$ ,  $I_C = 20 \text{ mA}$ ,  $Z_O = 50 \Omega$ )

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.220	-101.8	13.13	106.0	0.0532	71.5	0.401	-48.6
400	0.135	-149.0	7.08	90.8	0.0946	73.6	0.277	-49.0
600	0.120	175.1	4.83	82.2	0.137	72.6	0.239	-50.1
800	0.132	148.0	3.70	75.5	0.178	70.8	0.221	-53.4
1000	0.155	129.6	3.02	69.5	0.220	68.2	0.212	-57.9
1200	0.174	117.3	2.58	63.9	0.258	65.6	0.205	-63.1
1400	0.196	105.5	2.26	58.8	0.296	62.9	0.201	-69.1
1600	0.225	97.8	2.04	54.1	0.331	60.3	0.197	-75.7
1800	0.246	92.0	1.86	50.0	0.364	57.5	0.193	-82.1
2000	0.267	84.5	1.72	45.7	0.397	54.7	0.190	-89.4



Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g

## Cautions

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# HITACHI

## Hitachi, Ltd.

Semiconductor & Integrated Circuits.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL      North America      : <http://semiconductor.hitachi.com/>  
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## For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX

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